



40V PNP SMALL SIGNAL TRANSISTOR IN X1-DFN1006-3

Features

- BVcEo > -40V
- Ic = -200mA High Collector Current
- P_D = 1000mW Power Dissipation
- 0.60mm² Package Footprint, 13 Times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type DIODES™ MMBT3904LP
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

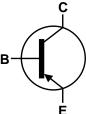
Package: X1-DFN1006-3

- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0008 grams (Approximate)

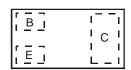




Bottom View



Device Symbol



Top View Device Schematic

Ordering Information (Note 4)

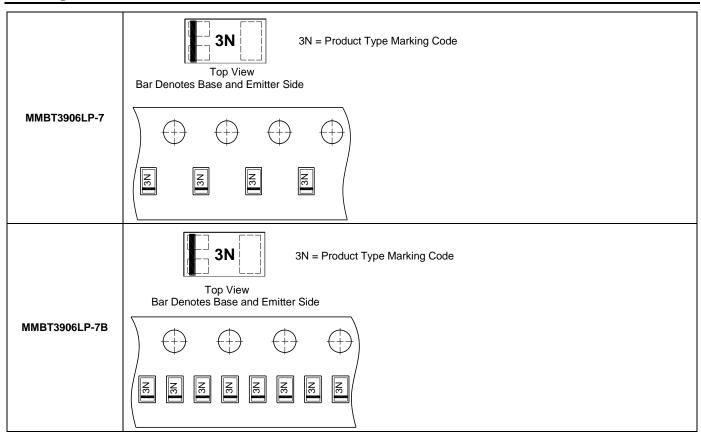
Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Pac	king
Fait Number	Fackage	Warking	Reel Size (Iliches)	rape width (IIIII)	Qty.	Carrier
MMBT3906LP-7	X1-DFN1006-3	3N	7	8	3,000	Reel
MMBT3906LP-7B	X1-DFN1006-3	3N	7	8	10,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information





Absolute Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vсво	-40	V
Collector-Emitter Voltage	VCEO	-40	V
Emitter-Base Voltage	VEBO	-6	V
Collector Current	Ic	-200	mA
Peak Collector Current	Ісм	-200	mA

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D-	400	mW	
Fower Dissipation	(Note 6)	PD	1000		
Thermal Desistance Junction to Ambient	(Note 5)	Devi	310	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	120		
Thermal Resistance, Junction to Case (Note 5)		Rejc	60	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Notes:

For the device mounted on minimum recommended pad layout 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition.
 Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics

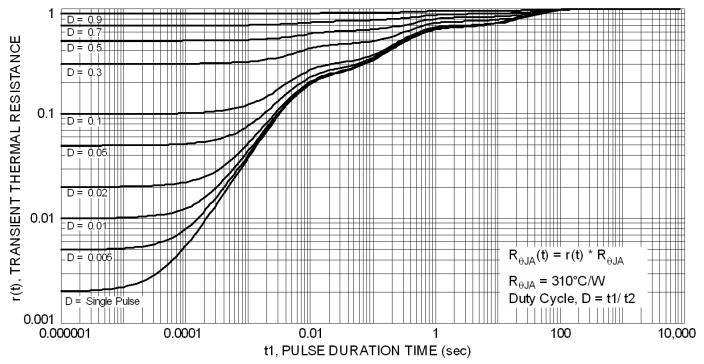


Fig. 1 Transient Thermal Resistance

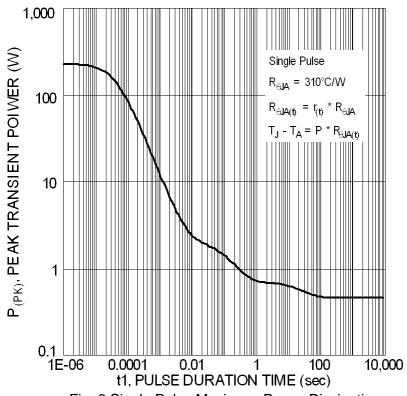


Fig. 2 Single Pulse Maximum Power Dissipation



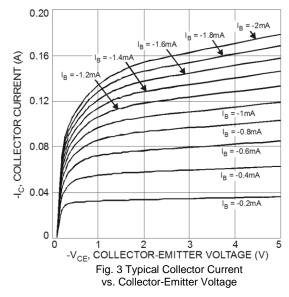
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	ВУсво	-40	_	V	Ic = -100μA
Collector-Emitter Breakdown Voltage (Note 8)	BVceo	-40	_	V	Ic = -10.0mA
Emitter-Base Breakdown Voltage	BVEBO	-6	_	V	I _E = -100μA
Collector Cutoff Current	ICEX	_	-50	nA	Vce = -30V, VeB(off) = -3.0V
Collector Cutoff Current	Ісво	_	-50	nA	VcB = -30V
Base Cutoff Current	I _{BL}	_	-50	nA	V _{CE} = -30V, V _{EB(off)} = -3.0V
ON CHARACTERISTICS (Note 8)					
		60	_		Ic = -100μA, Vcε = -1.0V
		80	_		Ic = -1.0mA, VcE = -1.0V
DC Current Gain	hfE	100	300	_	Ic = -10mA, VcE = -1.0V
		60	_		Ic = -50mA, VcE = -1.0V
		30	_		Ic = -100mA, VcE = -1.0V
Collector-Emitter Saturation Voltage	V-= ()	_	-0.25	V	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$
Collector-Entitler Saturation Voltage	V _{CE(sat)}	_	-0.40	V	$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE} (sat)	-0.65	-0.85	V	$I_C = -10mA$, $I_B = -1.0mA$
base-Emiller Saturation Voltage		_	-0.95		$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	Cobo	_	4.5	pF	V _{CB} = -5.0V, f = 1.0MHz
Input Capacitance	Cibo	_	10	pF	V _{EB} = -0.5V, f = 1.0MHz
Input Impedance	hie	2	12	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	10	x 10 ⁻⁴	$V_{CE} = -10V, I_{C} = -1.0mA$
Small Signal Current Gain	h _{fe}	100	400	_	f = 1.0kHz
Output Admittance	hoe	3	60	μS	
Current Gain-Bandwidth Product	f⊤	300	_	MHz	V _{CE} = -20V, I _C = -10mA f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	td	_	35	ns	
Rise Time	tr	_	35	ns	$V_{CC} = -3.0V, I_{C} = -10mA$
Storage Time	ts	_	225	ns	$I_{B1} = -I_{B2} = -1.0 \text{mA}$
Fall Time	t _f	_	75	ns	

Note: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



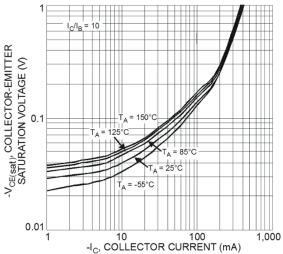


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

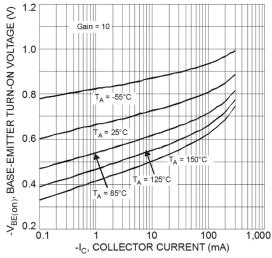


Fig. 7 Typical Base-Emitter Turn-On Voltage vs. Collector Current

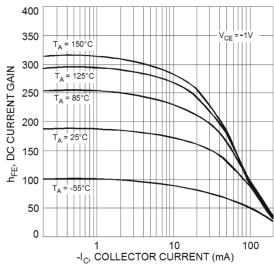


Fig. 4 Typical DC Current vs. Collector Current

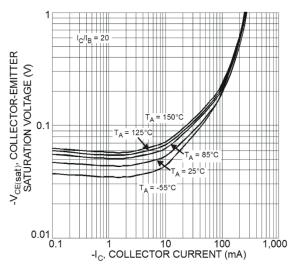


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

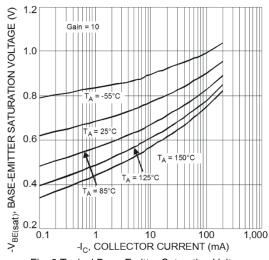


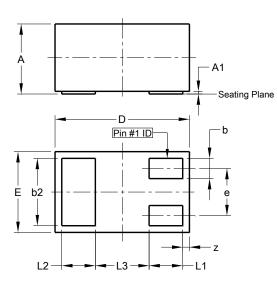
Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1006-3

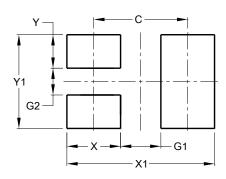


X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	-	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	•	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1006-3



Dimensions	value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Υ	0.25
Y1	0.70



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